

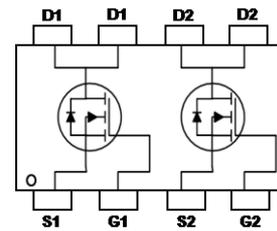
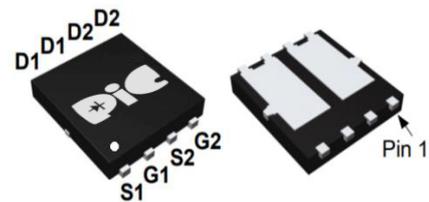
### ➤ General Description

This PAN32TY04YB Dual N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent  $R_{ds(On)}$  performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

### ➤ Feature

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent  $CdV/dt$  effect decline
- Advanced high cell density Trench technology
- DFN5x6A-EP2 package design

### ➤ DFN5X6A-EP2



### ➤ Application

- DC/DC Primary Side Switch
- Industrial Synchronous
- Rectification Load Switch
- DC/DC Converters

### ➤ Absolute Maximum Ratings

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sub>1</sub>	$I_D@T_C=25^\circ C$	35	A
Continuous Drain Current <sub>1</sub>	$I_D@T_C=100^\circ C$	24.7	A
Continuous Drain Current <sub>1</sub>	$I_D@T_A=25^\circ C$	10.6	A
Continuous Drain Current <sub>1</sub>	$I_D@T_A=70^\circ C$	8.5	A
Pulsed Drain Current <sub>2</sub>	$I_{DM}$	92	A
Single Pulse Avalanche Energy <sub>3</sub>	EAS	57.8	mJ
Avalanche Current	$I_{AS}$	34	A
Total Power Dissipation <sub>4</sub>	$P_D@T_C=25^\circ C$	19.2	W
Total Power Dissipation <sub>4</sub>	$P_D@T_A=25^\circ C$	1.42	W
Storage Temperature Range	$T_{STG}$	-55 to 150	$^\circ C$
Operating Junction Temperature Range	$T_J$	-55 to 150	$^\circ C$
Thermal Resistance Junction-Ambient <sub>1</sub>	$R_{\theta JA}$	62	$^\circ C/W$
Thermal Resistance Junction-Case <sub>1</sub>	$R_{\theta JC}$	6.5	$^\circ C/W$

### ➤ N-Channel Electrical Characteristics (T<sub>J</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
Static Drain-Source On-Resistance <sup>2</sup>	$R_{DS(ON)}$	$V_{GS}=10V, I_D=12A$	---	6.5	8.5	mΩ
		$V_{GS}=4.5V, I_D=10A$	---	11	14	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.5	2.5	V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ C$	---	---	1	uA
		$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ C$	---	---	5	
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	±100	nA
Forward Transconductance	$g_{fs}$	$V_{DS}=5V, I_D=15A$	---	38	---	S
Gate Resistance	$R_g$	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	---	1.7	---	Ω
Total Gate Charge (4.5V)	$Q_g$	$V_{DS}=15V, V_{GS}=4.5V, I_D=12A$	---	12.8	---	nC
Gate-Source Charge	$Q_{gs}$		---	3.3	---	
Gate-Drain Charge	$Q_{gd}$		---	6.5	---	
Turn-On Delay Time	$T_{d(on)}$	$V_{DD}=15V, V_{GS}=10V, R_G=3.3\Omega, I_D=12A$	---	4.5	---	ns
Rise Time	$T_r$		---	10.9	---	
Turn-Off Delay Time	$T_{d(off)}$		---	25.6	---	
Fall Time	$T_f$		---	9.5	---	
Input Capacitance	$C_{iss}$	$V_{DS}=15V, V_{GS}=0V, f=1MHz$	---	1317	---	pF
Output Capacitance	$C_{oss}$		---	163	---	
Reverse Transfer Capacitance	$C_{rss}$		---	131	---	

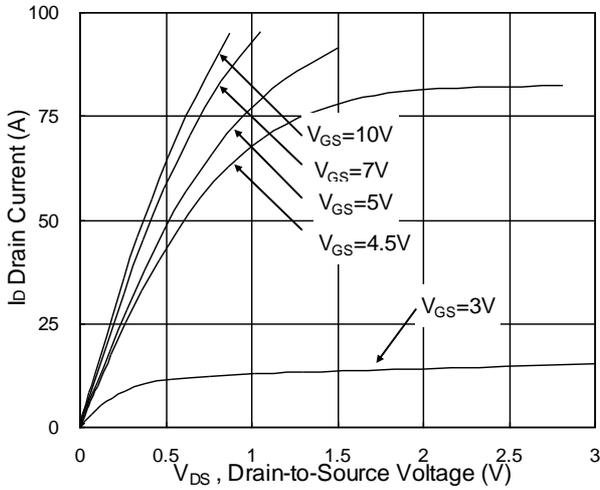
### ➤ Diode Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Continuous Source Current <sup>1,5</sup>	$I_S$	$V_G=V_D=0V, \text{Force Current}$	---	---	15	A
Diode Forward Voltage <sup>2</sup>	$V_{SD}$	$V_{GS}=0V, I_S=1A, T_J=25^\circ C$	---	---	1	V
Reverse Recovery Time	$t_{rr}$	$I_F=15A, di/dt=100A/\mu s, T_J=25^\circ C$	---	9.2	---	nS
Reverse Recovery Charge	$Q_{rr}$		---	2	---	nC

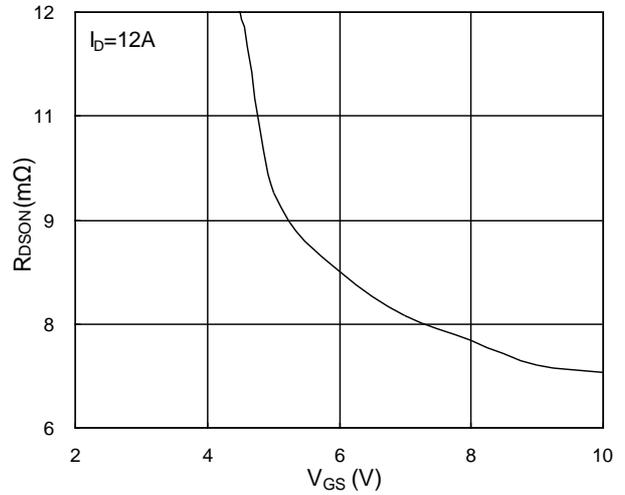
Note :

- 1.Pulse width limited by maximum junction temperature.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=34A$
- 4.Ensure that the channel temperature does not exceed 150°C.
- 5.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.

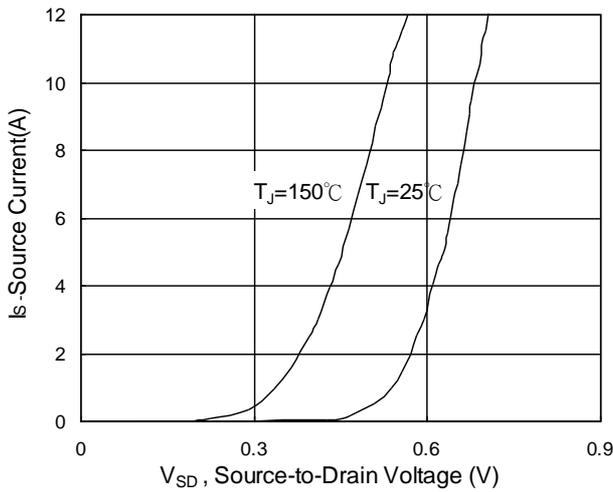
### ➤ Typical Characteristics



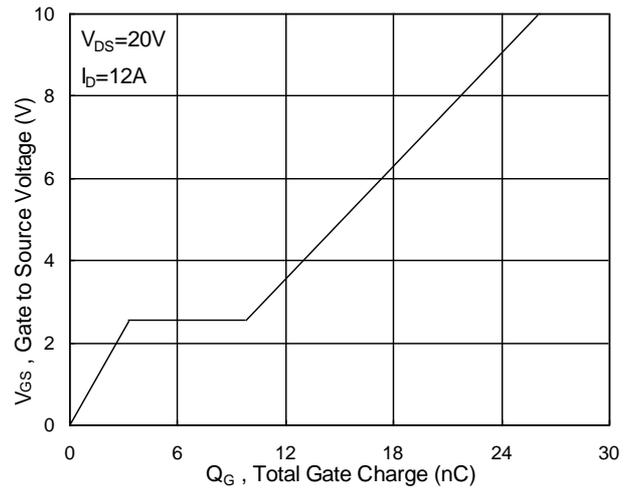
**Fig.1 Typical Output Characteristics**



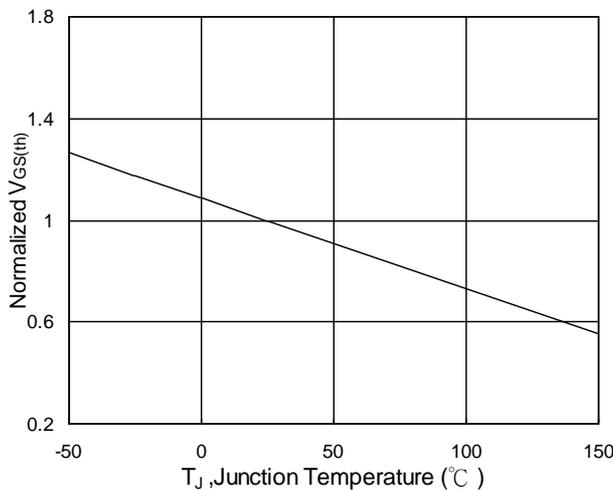
**Fig.2 On-Resistance vs G-S Voltage**



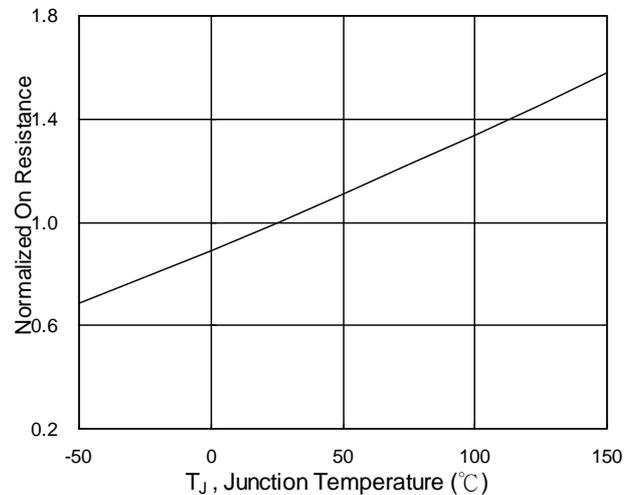
**Fig.3 Source Drain Forward Characteristics**



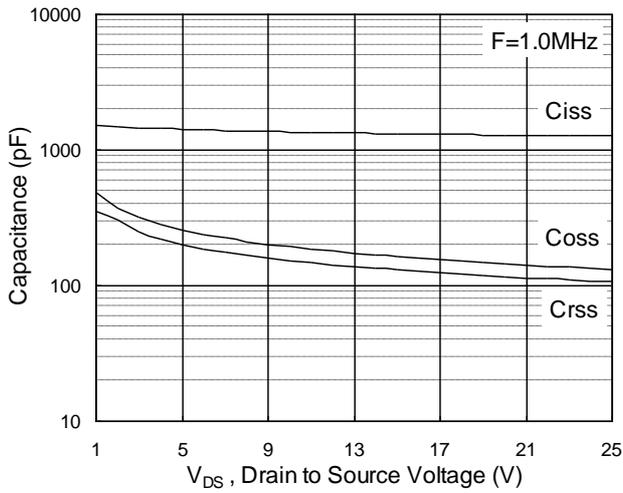
**Fig.4 Gate-Charge Characteristics**



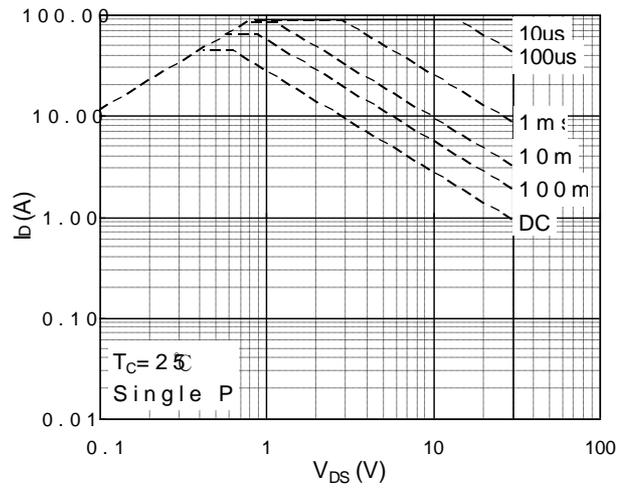
**Fig.5 Normalized  $V_{GS(th)}$  vs  $T_J$**



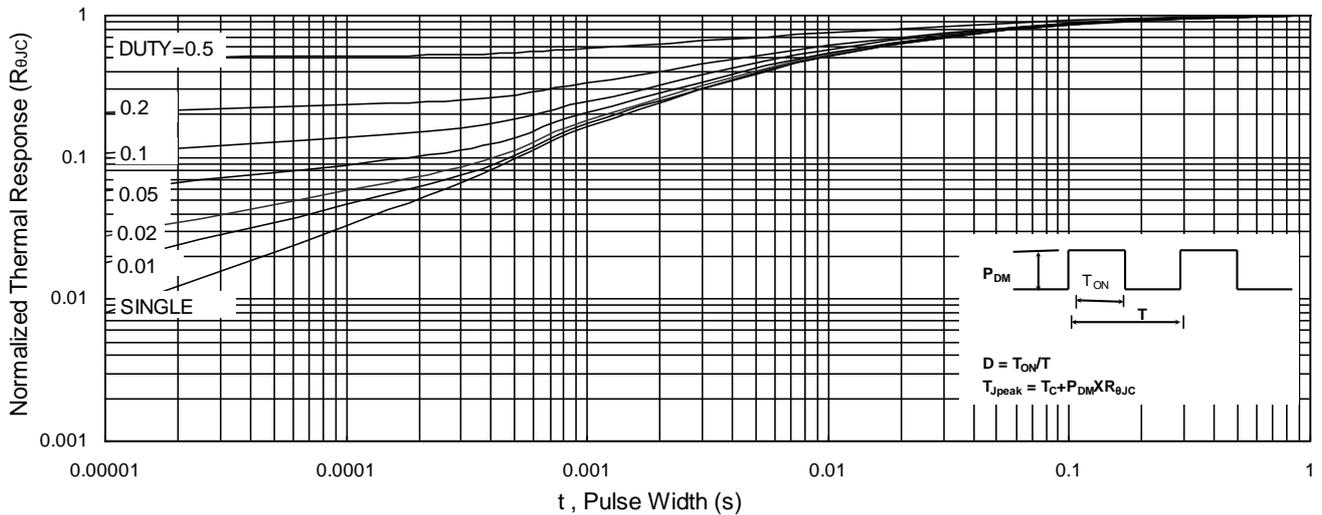
**Fig.6 Normalized  $R_{DS(on)}$  vs  $T_J$**



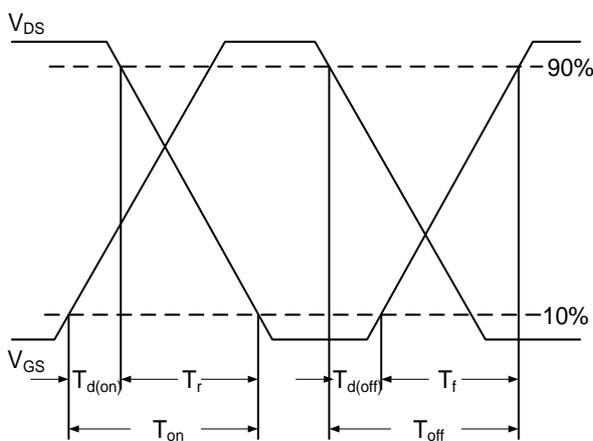
**Fig.7 Capacitance**



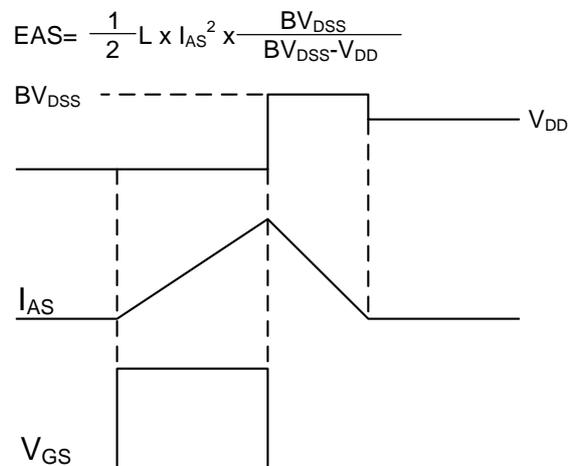
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**

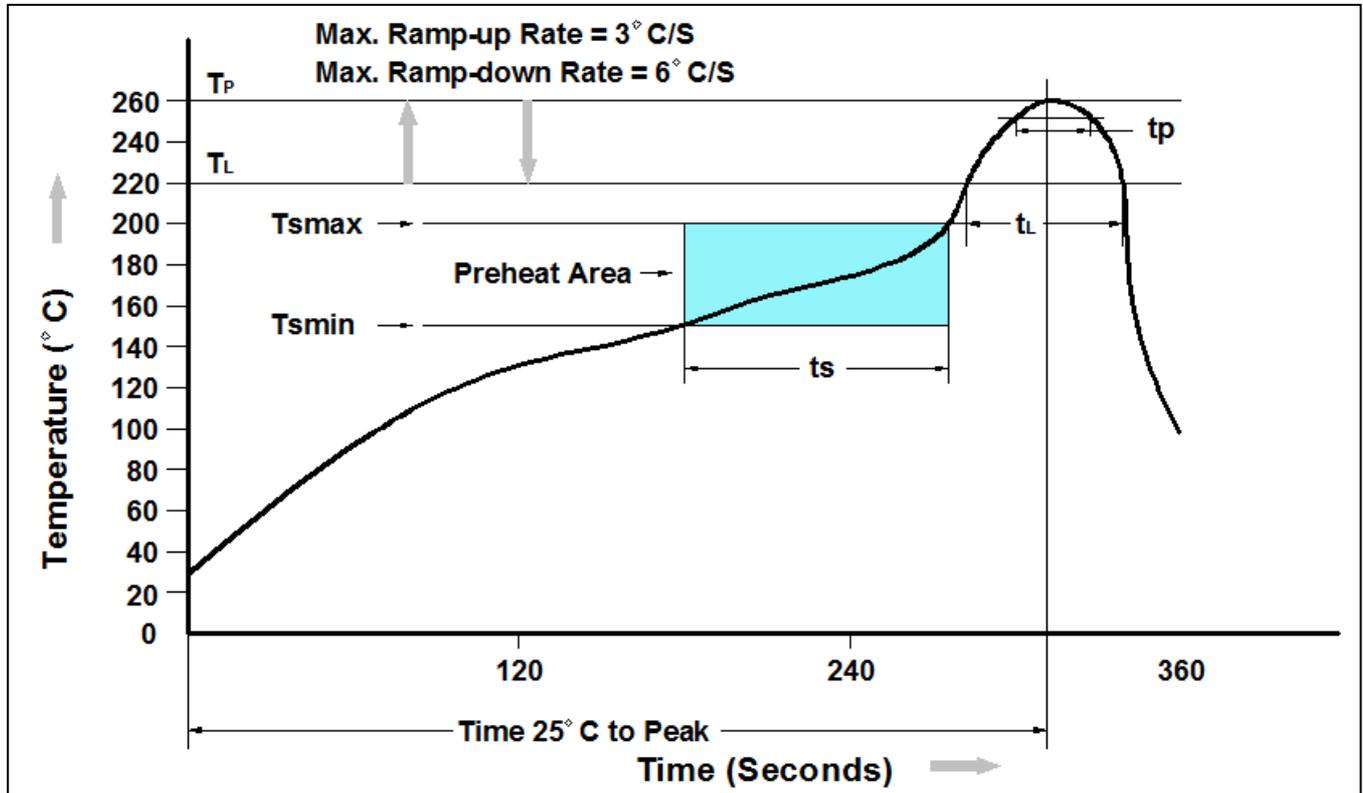


**Fig.10 Switching Time Waveform**



**Fig.11 Unclamped Inductive Switching Waveform**

### ➤ Recommend IR Reflow Soldering Thermal Profile

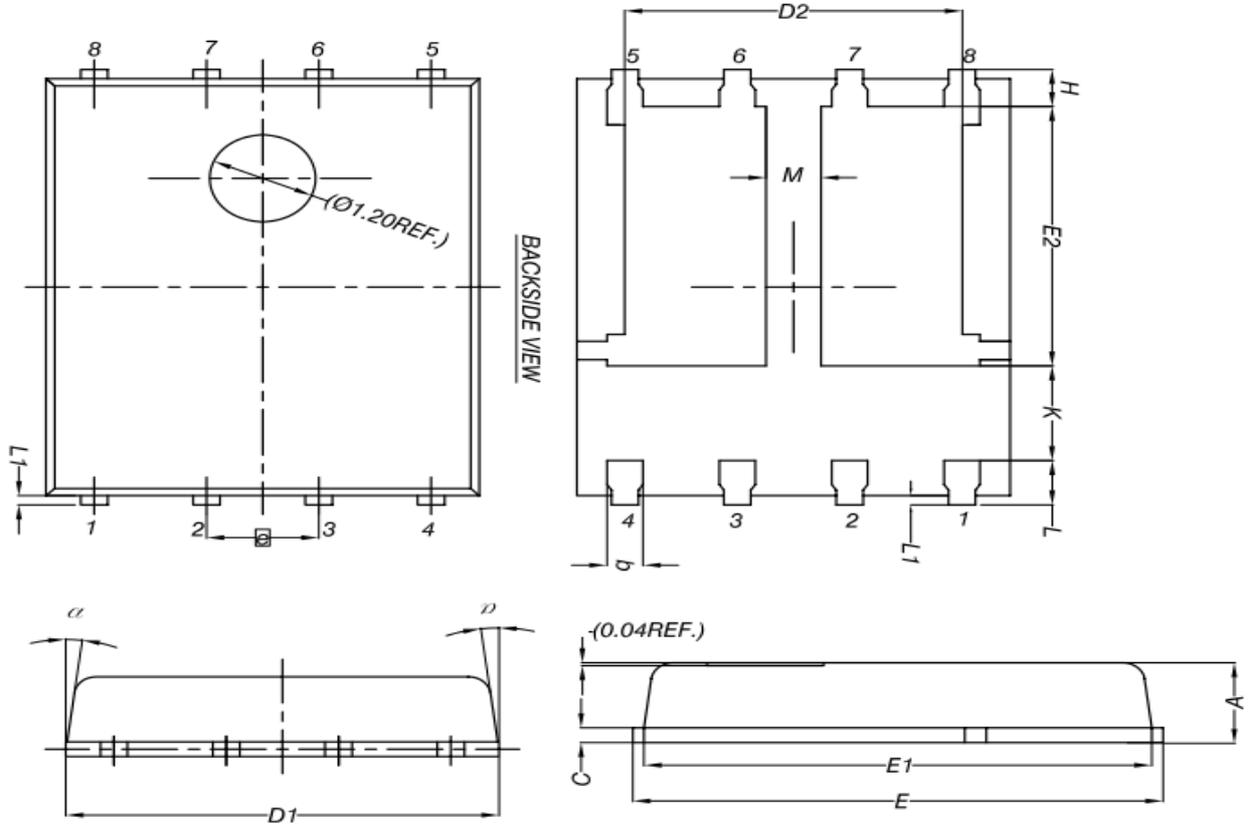


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T <sub>smin</sub> )	150°C
Temperature Max. (T <sub>smax</sub> )	200°C
Time (t <sub>s</sub> ) from (T <sub>smin</sub> to T <sub>smax</sub> )	60-120 seconds
Average Ramp-up Rate (t <sub>L</sub> to t <sub>P</sub> )	3°C/second max.
Liquidous Temperature (T <sub>L</sub> )	217°C
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t <sub>P</sub> ) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

### ➤ Ordering Information

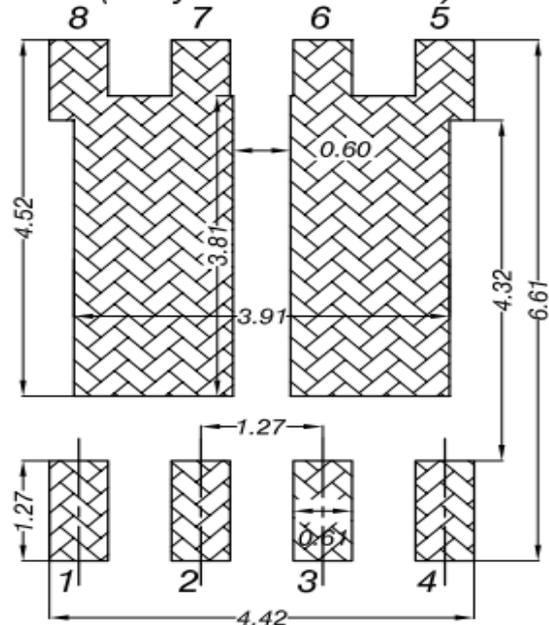
Part Number	Description	Quantity
PAN32TY04YB	DFN5X6A-EP2 Reel	3000 pcs

### ➤ Package Information ( DFN5X6A-EP2 )



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
M	0.50	-	-
α	0°	-	12°

### Land Pattern (Only for Reference)



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